Achieving accuracy in charge carrier mobility modelling in silicon
Mnatsakanov, T.T.; Gresserov, B.N.; Pomortseva, L.I. Automation, simulation & measurement : ASM'91 : 3rd biennal conference, Tallinn, October 7-11, 1991. Section S / Tallinn Technical University 1992 / p. 89-94: ill

AFM and SEM investigations of ion beam synthesized Mg2Si precipitates in Si substrates
Angelov, Christo; **Mikli, Valdek**; Amov, Blagoj; Goranova, E. Journal of optoelectronics and advanced materials 2005 / 1, p. 369-373 https://old.joam.inoe.ro/arhiva/pdf7_1/Angelov3.pdf

Analyses of frequency dependencies of Q factor for planar inductors on silicon
Jankovskis, Janis; Yurshevich, Valentins; Rankis, Gunars BEC'98 : the 6th Biennial Conference on Electronics and Microsystems Technology, October 7-9, 1998, Tallinn, Estonia : proceedings 1998 / p. 231-234

Band gap engineering by cationic substitution in Sn(Zr1−xTix)Se3 alloy for bottom sub-cell application in solar cells
Kondrotas, Rokas; Pakstas, Vidas; Franckevicius, Marius; Suchodolskis, Arturas; Tumenas, Saulius; Jasinskas, Vidmantas; Juskenas, Remigijus; Krotkus, Arunas; **Muska, Katri**; **Kauk-Kuusik, Marit** Journal of materials chemistry A 2023 / p. 26488–26498 : ill https://doi.org/10.1039/D3TA05550G Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Comparative ellipsometric and ion beam analytical studies on ion beam crystallized silicon implanted with Zn and Pb ions
Lohner, Tivador; Angelov, Christo; **Mikli, Valdek** Thin solid films 2008 / 22, p. 8009-8012 https://www.sciencedirect.com/science/article/pii/S0040609008003660

Corrected accounting of electron-hole scattering in cross-term current equations for Si and SiC
Velmre, Enn; **Udal, Andres** Physica scripta 1999 / Proceedings of 18th Nordic Semiconductor Meeting, Linköping, Sweden, June 7-10, 1998, ISBN 91-87308-71-1, p. 193-197: ill https://ui.adsabs.harvard.edu/abs/1999PhST...79..193V/abstract

Corrected accounting of electron-hole scattering in cross-term current equations for Si and SiC
Velmre, Enn; **Udal, Andres** 18th Nordic Semiconductor Meeting, Linköping, June 7-10, 1998 : abstracts 1998 / p. F-88: ill https://iopscience.iop.org/article/10.1238/Physica.Topical.079a00193

Correlation between the UV-reflectance spectra and the structure of poly-Si films obtained by aluminium induced crystallization
Dimova-Malinovska, D.; Angelov, O.; Sendova-Vassileva, M.; **Mikli, Valdek** Journal of optoelectronics and advanced materials 2009 / 9, p. 1079-1085 https://www.researchgate.net/publication/288122478_Correlation_between_the_UV-reflectance_spectra_and_the_structure_of_poly-Si_films_obtained_by_Aluminium_Induced_Crystallization

A double-emitter silicon differential strain sensitive transistor with an accelerating field in its base
Babichev, G.G.; Kozlovskii, S.I.; Romanov, V.A.; Sharan, N.N. BEC'98 : the 6th Biennial Conference on Electronics and Microsystems Technology, October 7-9, 1998, Tallinn, Estonia : proceedings 1998 / p. 263-264: ill

Eesti teadlased loovad tuleviku päikesepaneeli
Grossberg-Kuusk, Maarja postimees.ee 2025 / lk. 6 https://arvamus.postimees.ee/8276259/maarja-grossberg-kuusk-eesti-teadlased-loovad-tuleviku-paikesepaneeli https://dea.digar.ee/article/postimees/2025/06/28/7.4

Effect of calcium to silicon ratio on the microstructure of hydrated calcium silicate gels prepared under medium alkalinity
Ba, Haojing; Li, Jiajie; Ni, Wen; Li, Ying; Ju, Yongjian; Zhao, Ben; Wen, Guoping; **Hitch, Michael William** Construction and building materials 2023 / art. 131240, 11 p.: ill https://doi.org/10.1016/j.conbuildmat.2023.131240

Effect of silica precursor on the synthesis of Zn2SiO4-based material
Rojas Hernandez, Rocio Estefania; **Hussainova, Irina**; **Necib, Jallouli** Proceedings of the Estonian Academy of Sciences 2025 / p. 217-221 https://doi.org/10.3176/proc.2025.2.24

Electrochemical deposition of thin polypyrrole films on silicon substrates
Intelmann, Carl Matthias; **Sõritski, Vitali**; Tsankov, Dimiter; Hinrichs, Karsten; Rappich, Jörg 5th ISE Spring Meeting : Dublin (Ireland), 01.-04.05.07 2007 / ? p

Electrochemically deposited ultrathin polypyrrole films on silicon
Intelmann, Carl Matthias; **Sõritski, Vitali**; Tsankov, Dimiter; Hinrichs, Karsten; Rappich, Jörg GDCh (German Chemical Society) - YoungChemists : Spring Symposium 2007 : Chemnitz (Germany), 22.-24.03.07 2007 / ? p

From virtual characterization to test-chips : DFM analysis through pattern enumeration
Martins, Mayler G.A.; **Pagliarini, Samuel Nascimento**; Isgenc, Mehmet Meric; Pileggi, Larry IEEE transactions on computer-aided design of integrated circuits and systems 2020 / p. 520-532 https://doi.org//10.1109/TCAD.2018.2889772

High phonon-drag thermoelectric efficiency of SiC at low temperatures
Velmre, Enn; **Udal, Andres**; Grivickas, Vytautas Final program of the 10th International Conference on SiC and Related Materials : ICSCRM'2003 : Lyon, France, Oct. 5-10, 2003 2003 / p. ThP4-13 https://www.researchgate.net/publication/240834700_High_Phonon-

Drag_Thermoelectric_Efficiency_of_SiC_at_Low_Temperatures

Hydrogen interaction with point defects in the Si-SiO2 structures and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Abru, Uno; Medvid, A. Solid state phenomena 2008 / p. 345-350 https://www.scientific.net/SSP.131-133.345

Impurity interaction with point defects in the Si-SiO2 structures and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Medvid, A. Materials science and engineering : B 2006 / p. 222-226 : ill https://www.sciencedirect.com/science/article/pii/S0921510706004375

Influence of differently formed interfacial aluminium oxide on the structural properties of poly-Si films prepared by aluminium induced crystallisation
Dimova-Malinovska, D.; Nichev, H.; Angelov, O.; Sendova-Vassileva, M.; Sendova, M.; **Mikli, Valdek** Journal of optoelectronics and advanced materials 2007 / 2, p. 359-362

Influence of excitonic scattering on charge carrier ambipolar diffusion in silicon
Udal, Andres; **Velmre, Enn** ESSDERC'97 : proceedings of the 27th European Solid-State Device Research Conference, Stuttgart, Germany, 22-24 September 1997 1997 / p. 212-215: ill https://ieeexplore.ieee.org/stamp/stamp.jsp?tp=&arnumber=1503333
https://doi.org////10.1109/ESSDERC.1997.194403

Interaction between point defects in the Si-Si=2 system
Kropman, Daniel; Kärner, T.; Samoson, Ago; Heinmaa, I.; **Mellikov, Enn** Nuclear instruments & methods in physics research. Section B 2002 / p. 78-82 https://www.sciencedirect.com/science/article/pii/S0168583X0100862X

Interaction between point defects in the Si-SiO2 system during the process of its formation
Kropman, Daniel; Kärner, T.; Samoson, Ago; Heidmaa, I.; Ugaste, Ülo; **Mellikov, Enn** Defect and Diffusion Forum 2001 / p. 1737-1744 https://www.sciencedirect.com/science/article/abs/pii/S0168583X0100862X

Interaction of point defects with impurities in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; Kärner, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej Solid state phenomena 2011 / p. 263-266 https://www.sciencedirect.com/science/article/pii/S0040609009014564

Interaction of point defects with impurities in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; Kärner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos Physica status solidi (c) 2011 / p. 694-696 : ill https://www.sciencedirect.com/science/article/pii/S0040609009014564

Interaktsioon punktdefektide ja lisandite vahel süsteemis Si-SiO2 ja nende mõju piirpinna omadustele : [ettekande sisukokkuvõte]
Kropman, Daniel; Kärner, T.; Heinmaa, I. Eesti Füüsika Seltsi aastaraamat 2008 2009 / lk. 119-120

Jaan Raik: Computers must undergo a revolution in order to continue their rapid development
Raik, Jaan Estonian Centre of Excellence in ICT Research 2021 / p. 43-47 : ill http://www.digar.ee/id/nlib-digar:634779
https://www.ester.ee/record=b5456158*est

Jaan Raik: kiibidisain aitaks saada Eestil jõukaks tehnoloogiamaaks
Maidla, Margus novaator.err.ee 2023

Kassikuld võib osutuda elektroonikatööstuses kullast kallimaks
Kristmann, Katriin novaator.err.ee 2024 Kassikuld võib osutuda elektroonikatööstuses kullast kallimaks

Keemia tee klaasist ränisse : tänavune Nobeli keemiaauhind seab õigluse jalule keemiateoreetikute ja arvutikeemikute hulgas
Strandberg, Marek Sirp 2013 / lk. 26 https://www.sirp.ee/s1-artiklid/c21-teadus/2013-10-17-20-15-58-2/

Kleenukesed päikeseelemendid aitaks vältida ränipaneele ootavat kriisi
Sibinski, Maciej novaator.err.ee 2024 Kleenukesed päikeseelemendid aitaks vältida ränipaneele ootavat kriisi

Modeling of charge carrier non-isothermal transport parameters in silicon
Velmre, Enn; **Udal, Andres** BEC'98 : the 6th Biennial Conference on Electronics and Microsystems Technology, October 7-9, 1998, Tallinn, Estonia : proceedings 1998 / p. 71-74: ill

Modelling of charge carrier non-isothermal transport in silicon and silicon carbide
Velmre, Enn; **Udal, Andres** Proceedings of the Estonian Academy of Sciences. Engineering 2000 / p. 144-154 : ill
https://artiklid.elnet.ee/record=b1004044*est

Modular synthesis of (Borylmethyl)silanes through orthogonal functionalization of a carbon atom

Chowdhury, Rajdip; **Elek, Gábor Zoltán**; Meana-Baamonde, B.; Mendoza, Abraham Organic letters 2023 / p. 1935-1940 : ill https://doi.org/10.1021/acs.orglett.3c00474 Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Must räni tõi helged lootused
Krustok, Jüri Eesti Päevaleht 2000 / 19. veebr., lk. 23 https://artiklid.elnet.ee/record=b1637055*est

Point defects interaction with extended defects and impurities and its influence on the Si-SiO2 system properties
Kropman, Daniel; Arbu, Uno; Kärner, T.; Ugaste, Ülo; **Mellikov, Enn**; **Kauk, Marit**; Heinmaa, I.; **Samoson, Ago**; Medvid, A. Gettering and defect engineering in semiconductor technology. XI 2005 / p. 333-338 : ill https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO_2_System_Properties

Point defects interaction with extended defects in the Si-SiO2 system [Electronic resource]
Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn** Proceedings IVC-16 : Venice, 2004 2004 / p. SS1-TuP394 [CD-ROM] https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO_2_System_Properties

Porphyrin-based hybrid nanohelices : cooperative effect between molecular and supramolecular chirality on amplified optical activity
Anfar, Zakaria; Kuppan, Balamurugan; Scalabre, Antoine; Nag, Rahul; Pouget, Emilie; Nlate, Sylvain; Magna, Gabriele; Di Filippo, Ilaria; Monti, Donato; Naitana, Mario L.; Stefanelli, Manuela; **Nikonovich, Tatsiana**; **Borovkov, Victor**; **Aav, Riina**; Paolesse, Roberto; Oda, Reiko The journal of physical chemistry B 2024 / p. 1550-1556 https://doi.org/10.1021/acs.jpcb.3c07153 Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Predictable quantum efficient detector. I, Photodiodes and predicted responsivity
Sildoja, Meelis; Manoocheri, Farshid; Merimaa, Mikko; Ikonen, Erkki; Müller, Ingmar; Werner, Lutz; Gran, Jarle; **Kübarsepp, Toomas**; Smid, Marek; Rastello, Maria Luisa Metrologia 2013 / p. 385-394 : ill https://doi.org/10.1088/0026-1394/50/4/385 https://cris.vtt.fi/en/publications/predictable-quantum-efficient-detector-i-photodiodes-and-predicte Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Production of silicon free master alloys in Estonia
Gorkunov, Valeri; **Munter, Rein** Scientific proceedings of Riga Technical University. 1. [series], Material science and applied chemistry 2007 / p. 111-121

Päikeseenergeetika tulevikku kujundavad kilepinnad ja tandempaneelid
Piir, Rait novaator.err.ee 2023 Päikeseenergeetika tulevikku kujundavad kilepinnad ja tandempaneelid

Rapid prototyping of silicon structures by aid of laser and abrasive-jet machining
Kruusing, Arvi; Leppävuori, Seppo; Uusimäki, Antti; Uusimäki, M. Design, Test and Microfabrication of MEMS and MOEMS : 30 March-1 April, 1999, Paris, France 1999 / p. 870-878 : ill https://opticalengineering.spiedigitallibrary.org/conference-proceedings-of-spie/3680/0000/Rapid-prototyping-of-silicon-structures-by-aid-of-laser-and/10.1117/12.341285.full

Recombination behaviour at the ultra-thin polypyrrole film/silicon interface investigated by in-situ pulsed photoluminescence
Intelmann, Carl Matthias; Hinrichs, Karsten; **Sõritski, Vitali**; Yang, Florent; Rappich, Jörg Japanese journal of applied physics 2008 / 2, p. 554-557 https://iopscience.iop.org/article/10.1143/JJAP.47.554

Relationships between essential and non-essential elements in plants with different nutritional strategies and silicon absorption capacities : [manuscript]
Monei, Nthati Lilian; Benyr, V.; Heilmeier, Hermann; **Hitch, Michael William**; Wiche, Oliver The international journal of environment & health 2023

Review of - SiC wide-bandgap heterostructure properties as an alternate semiconductor material
Patankar, Udayan Sunil; Rajput Priti, J.; **Koel, Ants**; Nitnaware, V.N. International Conference on Inventive Research in Material Science and Technology, ICIRMCT 2018 : March 23-24, 2018 2018 / art. 020011 https://doi.org/10.1063/1.5038690 Conference proceedings at Scopus Article at Scopus Article at WOS

Selective laser melting of commercially pure silicon
Lai, Zhouyi; Guo, Ting; Zhang, Shengting; Kollo, Lauri; Attar, Hooyar; Wang, Zhi; **Prashanth, Konda Gokuldoss** Journal Wuhan University of Technology, Materials Science Edition 2022 / p. 1155 - 1165 https://doi.org/10.1007/s11595-022-2647-3 Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Silica granulates in concrete - dispersion and durability aspects
Lagerblad, Björn; **Utkin, Pjotr** 1993 https://www.ester.ee/record=b1025989*est

Szilicium planar technologiai eljaras szamitögepes stimulacioja

Rang, Toomas; Tarnay, K.; Masszi, F. Finommechanika, mikrotechnika: az Optikai, Akusztikai és Filmtechnikai Egyesület, a Híradástechnikai Tudományos Egyesület és a Méréstechnikai és Automatizálási Tudományos Egyesület lapja 1979 / p. 257-260

Strain relaxation mechanism in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; **Mellikov, Enn**; **Öpik, Andres**; **Lott, Kalju**; **Volobujeva, Olga**; Kärner, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A. Physica B : condensed matter 2009 / 23/24, p. 5153-5155 : ill

Stress relaxation mechanism by strain in the Si-SiO2 system and its influence on the interface properties
Kropman, Daniel; Seeman, Viktor; Dolgov, Sergei; Heinmaa, Ivo; Medvid, Artur Physica Status Solidi (C) Current Topics in Solid State Physics 2016 / p. 790 - 792 https://doi.org/10.1002/pssc.201600051 Journal metrics at Scopus Article at Scopus Article at WOS

Study of ion implanted Fe depth distribution in Si after pulsed ion beam treatment
Angelov, Christo; Georgiev, S.; Amov, Blagoj; Goranova, E.; **Mikli, Valdek**; Dezsi, I.; Kotai, E. Journal of optoelectronics and advanced materials 2007 / 2, p. 307-310
https://www.researchgate.net/publication/289186791_Study_of_the_ion_implanted_Fe_depth_distribution_in_Si_after_pulsed_ion_beam_treatment

Technonomics of manufacturing of silicon microsystems on WSI
Bubennikov, Alexander N.; Bubennikov, Alexander A. BEC'98 : the 6th Biennial Conference on Electronics and Microsystems Technology, October 7-9, 1998, Tallinn, Estonia : proceedings 1998 / p. 29-32: ill

The role of silicon in the hot dip galvanizing process
Sepper, Sirli; **Peetsalu, Priidu**; **Kulu, Priit**; **Saarna, Mart**; **Mikli, Valdek** Proceedings of the Estonian Academy of Sciences 2016 / p. 159-165 : ill https://artiklid.elnet.ee/record=b2768226*est https://doi.org/10.3176/proc.2016.2.11 Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Ursache und Wirkungsweise der Alkalireaktion in den aus estnischem Portlandölschieferzement hergestellten Betonen
Kikas, Verner; **Ojaste, Kalju**; **Raado, Lembi-Merike** ZKG International = Zement, Kalk, Gips international 1999 / 2, S. 106-111

Use of atomic-force microscopy for characterization of silicon, implated with heavy ions at high doses
Angelov, Christo; Groudev, P.; **Mikli, Valdek** Proceedings of 11th Conference "Materials for Information Tech. in the New Millenium" : ISCMP : Varna, 2001 2001 / p. 460-464

Valgustkiirgav räni
Krustok, Jüri Horisont 2001 / 1, lk. 12

Üliõhuke päikesepaneel avab energia tootmisele uued uksed
Alvela, Ain; **Krautmann, Robert** novaator.err.ee 2023 Üliõhuke päikesepaneel avab energia tootmisele uued uksed https://digikogu.taltech.ee/et/Item/e7e64926-5d49-40ad-8b3a-e225ea034f7d Ученый из Эстонии разрабатывает солнечные панели, которые изменят мир

Зависимость подвижности электронов и дырок от температуры и концентрации примеси в кремнии
Rang, Toomas; **Velmre, Enn** Анализ и моделирование технических устройств и систем АСУТП 1977 / с. 115-120 : ил https://www.ester.ee/record=b2190987*est https://digikogu.taltech.ee/et/Item/b7c66054-0b4f-4684-9453-442bc7e6e200

Изучение иммобилизации протеаз на кремнеземных материалах
Jegorov, H.R.; **Kivisilla, Külliki**; **Kipper, Heino**; **Erin, Anne**; **Köstner, Ado** Получение и применение иммобилизованных ферментов 1977 / с. 29-34 https://www.ester.ee/record=b1309558*est https://digikogu.taltech.ee/et/Item/67557c4a-b3ad-4f67-9fe9-4590245ecb73

Иммобилизация пепсина на кремнеземных материалах
Lukoševiciene, N.; **Sadauskas, P.**; **Ciurlis, T.**; **Kreen, Malle**; **Köstner, Ado** Получение и применение иммобилизованных ферментов 1977 / с. 57-66 : илл https://www.ester.ee/record=b1309558*est https://digikogu.taltech.ee/et/Item/67557c4a-b3ad-4f67-9fe9-4590245ecb73

Импульсно-плазменное легирование кремния сурьмой
Gavrilov, Aleksei; Katšurin, G.A. Электрофизические свойства полупроводниковых и диэлектрических материалов 1983 / с. 15-28 : ил https://www.ester.ee/record=b1291687*est https://digikogu.taltech.ee/et/Item/9447de85-407e-426e-843d-2f0c98097f4e

Импульсно-плазменный отжиг слоев кремния, имплантированных бором
Gavrilov, Aleksei; Katšurin, G.A. Электрофизические свойства полупроводниковых и диэлектрических материалов 1983 / с. 3-13 : ил https://www.ester.ee/record=b1291687*est https://digikogu.taltech.ee/et/Item/9447de85-407e-426e-843d-2f0c98097f4e

Инжекционные зависимости времени жизни неосновных носителей заряда в кремнии, легированном золотом и платиной
Udal, Andres Силовые быстродействующие полупроводниковые приборы : сборник статей. Часть II 1989 / с. 101-105 : ил., табл https://www.ester.ee/record=b1264433*est

Испульсное легирование кремния в сильноточном газовом разряде
Gavrilov, Aleksei; **Katšurin, G.A.** Письма в Журнал технической физики 1982 / с. 388-391 https://www.ester.ee/record=b2142356*est

Комплексное рентгенодифракционное исследование строения нарушенных слоев, обусловленных резкой кремнии
Milvidski, M.; Fomin, V.; **Meiler, Boriss** Физика и химия обработки материалов 1986 / с. 122-125
https://www.ester.ee/record=b1804847*est

Межфазное взаимодействие на контакте Ni-Si и Ni-GaAs
Meiler, Boriss Поверхность : физика, химия, механика 1985 / с. 62-67 : илл https://www.ester.ee/record=b2149829*est

Моделирование технологического процесса кремниевых силовых полупроводниковых приборов на ЭВМ
Rang, Toomas; **Velmre, Enn** Синтез и диагностика цифровых устройств и систем 1982 / с. 107-112 : ил
https://www.ester.ee/record=b1328194*est https://digikogu.taltech.ee/et/Item/febd586e-d7fa-4fbd-bf41-40576a75f94b

Наращивание поликристаллических слоев кремния на рельефную поверхность двуокиси кремния
Paat, Aadu; **Timma, Enn**; Trombovetski, A. Труды по физике : сборник статей. 6 1973 / с. 27-33 : илл
https://www.ester.ee/record=b2190564*est https://digikogu.taltech.ee/et/Item/020d3bce-d60f-45bd-aa8f-4906f2c1d0d6

О работе таблеточных фоторезисторов в кремнийорганической жидкости
Valdna, Vello Физическая химия соединений AIIBVI 1981 / с. 27-34 : илл https://www.ester.ee/record=b1533413*est
https://digikogu.taltech.ee/et/Item/dceb76ed-f60b-4ce9-b87e-618a41d25bb8

О целесообразности увеличения обратного напряжения силовых кремниевых диодов
Vaher, G.; **Tarma, Mati** Применение эпитаксиальной технологии в производстве силовых полупроводниковых приборов : сборник материалов Всесоюзного научно-технического семинара. Часть 1 1978 / с. 21-24
https://www.ester.ee/record=b1273235*est

Об определении экологических ПДК для минеральных форм азота, фосфора и кремния в водных объектах
Säärekõnno, Jüri Tallinna Tehnikaülikooli Toimetised 1990 / lk. 32-36: ill

Определение механической растираемости неорганических носителей
Köstner, Ado; **Kipper, Heino**; **Erin, Anne**; **Pedak, M.** Получение и применение иммобилизованных ферментов 1977 / с. 51-55 : илл https://www.ester.ee/record=b1309558*est https://digikogu.taltech.ee/et/Item/67557c4a-b3ad-4f67-9fe9-4590245ecb73

Отжиг имплантированных слоев кремния в плазме импульсного газового разряда
Gavrilov, Aleksei; Katšurin, G.A. Физика и техника полупроводников = Physics and technics of semiconductors 1981 / c.1232-1234 https://www.ester.ee/record=b1263919*est

Получение высокохромистых сплавов TiC-Fe-Cr, легированных кремнием
Kübarsepp, Jakob Порошковая металлургия = Powder metallurgy : ежемесячный научно-технический журнал 1986 / с. 65-69 : рис., таб https://www.ester.ee/record=b1645489*est

Получение иммобилизованной протеазы из Actinomyces vulgaris PA-II-4 и изучение некоторых ее свойств
Jegorov, H.R.; **Erin, Anne**; **Köstner, Ado**; **Loginova, L.G.**; **Golovina, I.G.** Получение и применение иммобилизованных ферментов 1977 / с. 35-41 : илл https://www.ester.ee/record=b1309558*est https://digikogu.taltech.ee/et/Item/67557c4a-b3ad-4f67-9fe9-4590245ecb73

Применение анодного окисления при исследовании электрофизических характеристик полупроводниковых структур "кремний на изоляторе"
Gavrilov, Aleksei Tallinna Tehnikaülikooli Toimetised 1990 / lk. 53-59: ill

Скорость связывания кремнезема песка в случае образования высоковольтных гидросиликатов кальция
Reiman, Värdi Сборник трудов (НИПИсиликатобетон) 1969 / с. [?] https://www.ester.ee/record=b1764431*est

Структура и глубина нарушенного слоя при грубой абразивной обработке монокристаллического кремния
Meiler, Boriss; Hatskevitš, M.; Ladotškin, A.; Fomin, V. Tallinna Tehnikaülikooli Toimetised 1990 / lk. 60-71: ill

Термообработка пластин кремния с нарушенным слоем
Meiler, Boriss; Ladotškin, A.; Fomin, V. Tallinna Tehnikaülikooli Toimetised 1990 / lk. 72-86: ill

Численное моделирование процесса выключения одномерных кремниевых тиристорных структур
Velmre, Enn; **Udal, Andres** Полупроводниковые приборы : сборник статей 1982 / с. 74-79
https://www.ester.ee/record=b1356516*est

Численное моделирование статических неизотермических процессов в кремниевых силовых диодных и тиристорных структурах в открытом состоянии
Velmre, Enn; **Udal, Andres**; **Freidin, Boris** Всесоюзный научно-технический семинар "Повышение параметров силовых полупроводниковых приборов на основе новых конструктивных решений и методов изготовления" (Запорожье, 1981) 1981 / с.37-38

Численное моделирование температурных распределений в кремниевых силовых полупроводниковых приборах при воздействии мощного импульса прямого тока
Velmre, Enn; **Nurste, Ivar**; **Freidin, Boris** Проблемы моделирования полупроводниковых структур и сложных схем на ЭВМ 1982 / с. 49-58 : ил https://www.ester.ee/record=b1339926*est https://www.etera.ee/zoom/121726/view?page=3&p=separate&search=true&tool=search

Численное моделирование физических процессов в одномерных кремниевых диодных структурах в стационарном режиме
Velmre, Enn; **Freidin, Boris**; **Udal, Andres** Алгоритмы и программы : информационный бюллетень 1980 / с.?